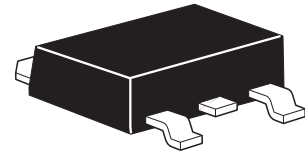


# ZXMP10A18K

## 100V DPAK P-channel enhancement mode MOSFET

### Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
-100	0.150 @ $V_{GS} = -10V$	-5.9
	0.190 @ $V_{GS} = -6V$	-5.2



### Description

This new generation trench MOSFET from Zetex features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

### Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- DPAK package

### Applications

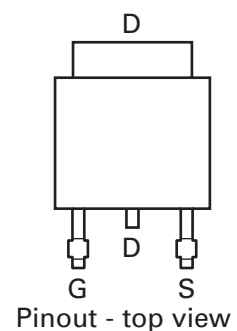
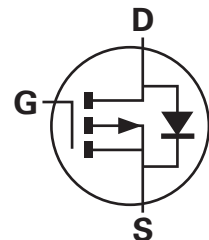
- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control

### Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP10A18KTC	13	16	2,500

### Device marking

ZXMP  
10A18



# ZXMP10A18K

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	$V_{DSS}$	-100	V
Gate-source voltage	$V_{GS}$	$\pm 20$	V
Continuous drain current @ $V_{GS} = 10V$ ; $T_{amb} = 25^{\circ}C^{(b)}$	$I_D$	-5.9	A
@ $V_{GS} = 10V$ ; $T_{amb} = 70^{\circ}C^{(b)}$		-4.7	
@ $V_{GS} = 10V$ ; $T_{amb} = 25^{\circ}C^{(a)}$		-3.8	
Pulsed drain current <sup>(c)</sup>	$I_{DM}$	-21.1	A
Continuous source current (body diode) <sup>(b)</sup>	$I_S$	-10	A
Pulsed source current (body diode) <sup>(c)</sup>	$I_{SM}$	-21.1	A
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$	$P_D$	4.3	W
Linear derating factor		34.4	mW/ $^{\circ}C$
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$	$P_D$	10.2	W
Linear derating factor		81.3	mW/ $^{\circ}C$
Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$	$P_D$	2.17	W
Linear derating factor		17.4	mW/ $^{\circ}C$
Operating and storage temperature range	$T_j, T_{stg}$	-55 to +150	$^{\circ}C$

## Thermal resistance

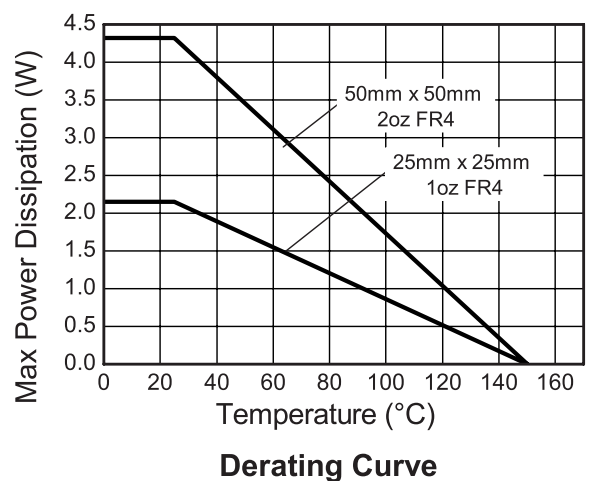
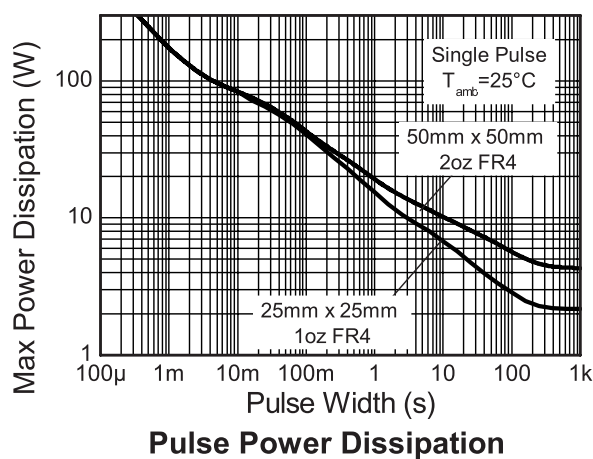
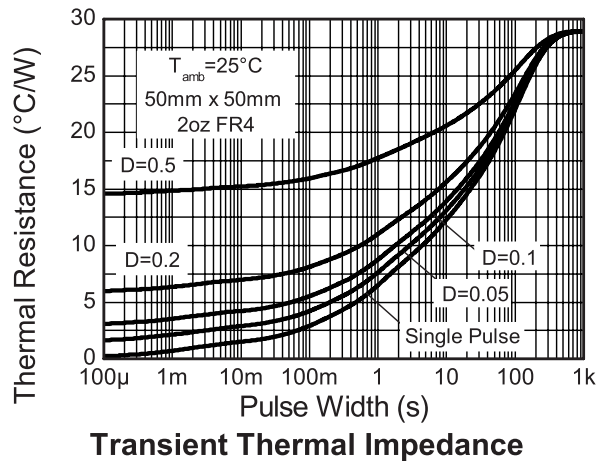
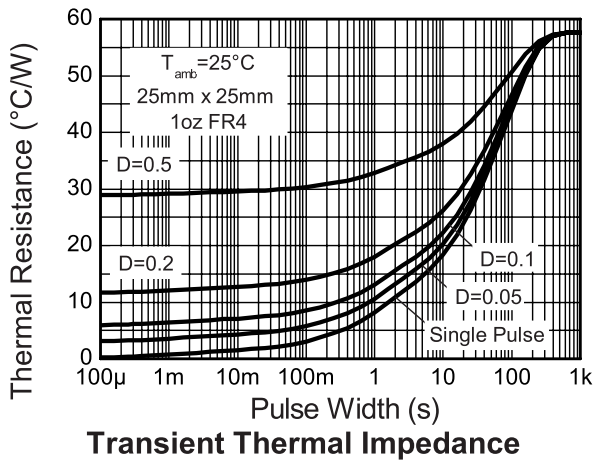
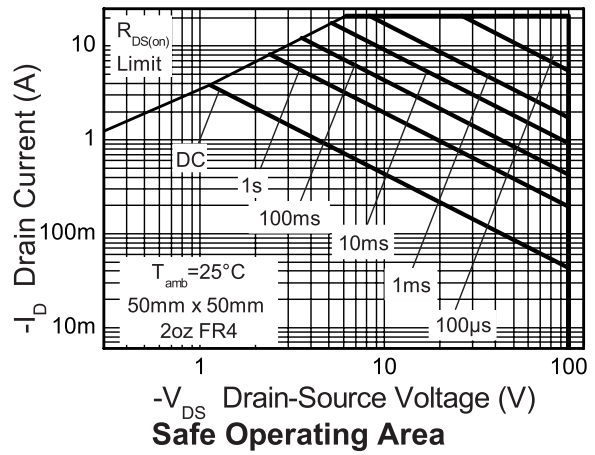
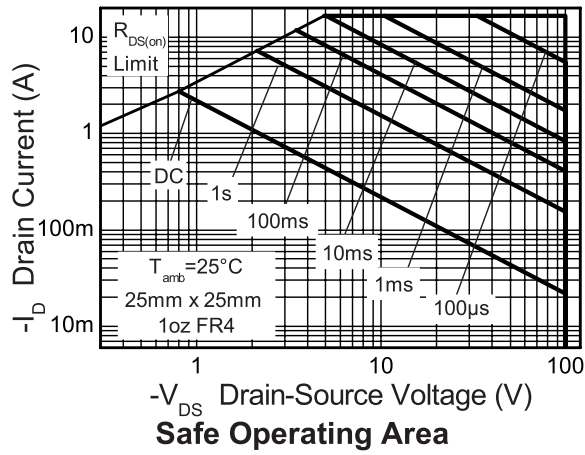
Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	29	$^{\circ}C/W$
Junction to ambient <sup>(b)</sup>	$R_{\theta JA}$	12.3	$^{\circ}C/W$
Junction to ambient <sup>(d)</sup>	$R_{\theta JA}$	57.6	$^{\circ}C/W$

### NOTES:

- (a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- (b) For a device surface mounted on FR4 PCB measured at  $t \leq 10$  sec.
- (c) Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB,  $D=0.02$  pulse width=300 $\mu s$  - pulse width limited by maximum junction temperature.
- (d) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

# ZXMP10A18K

## Thermal characteristics



# ZXMP10A18K

## Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
<b>Static</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	-100			V	$I_D = -250\mu\text{A}$ , $V_{GS} = 0\text{V}$
Zero gate voltage drain current	$I_{DSS}$			-1	$\mu\text{A}$	$V_{DS} = -100\text{V}$ , $V_{GS} = 0\text{V}$
Gate-body leakage	$I_{GSS}$			100	nA	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$
Gate-source threshold voltage	$V_{GS(th)}$	-2.0		-4.0	V	$I_D = -250\mu\text{A}$ , $V_{DS} = V_{GS}$
Static drain-source on-state resistance <sup>(*)</sup>	$R_{DS(on)}$			0.150 0.190	$\Omega$	$V_{GS} = -10\text{V}$ , $I_D = -2.8\text{A}$ $V_{GS} = -6\text{V}$ , $I_D = -2.4\text{A}$
Forward transconductance <sup>(*)(‡)</sup>	$g_{fs}$		6.0		S	$V_{DS} = -15\text{V}$ , $I_D = -2.8\text{A}$
<b>Dynamic<sup>(‡)</sup> (3)</b>						
Input capacitance	$C_{iss}$		1055		pF	$V_{DS} = -50\text{V}$ , $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output capacitance	$C_{oss}$		90		pF	
Reverse transfer capacitance	$C_{rss}$		76		pF	
<b>Switching<sup>(†)</sup> (‡)</b>						
Turn-on-delay time	$t_{d(on)}$		4.9		ns	$V_{DD} = -50\text{V}$ , $I_D = -1\text{A}$ $R_G = 6.0\Omega$ , $V_{GS} = -10\text{V}$
Rise time	$t_r$		6.8		ns	
Turn-off delay time	$t_{d(off)}$		33.9		ns	
Fall time	$t_f$		17.9		ns	
Total gate charge	$Q_g$		26.9		nC	$V_{DS} = -50\text{V}$ , $V_{GS} = -10\text{V}$ $I_D = -2.8\text{A}$
Gate-source charge	$Q_{gs}$		3.9		nC	
Gate drain charge	$Q_{gd}$		10.2		nC	
<b>Source-drain diode</b>						
Diode forward voltage <sup>(*)</sup>	$V_{SD}$		-0.85	-0.95	V	$T_j = 25^{\circ}\text{C}$ , $I_S = -3.5\text{A}$ , $V_{GS} = 0\text{V}$
Reverse recovery time <sup>(‡)</sup>	$t_{rr}$		49		ns	$T_j = 25^{\circ}\text{C}$ , $I_S = -2.8\text{A}$ , $di/dt = 100\text{A/ms}$
Reverse recovery charge <sup>(‡)</sup>	$Q_{rr}$		107		nC	

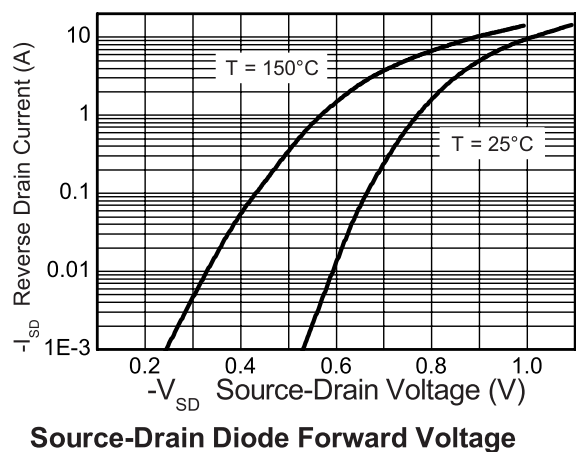
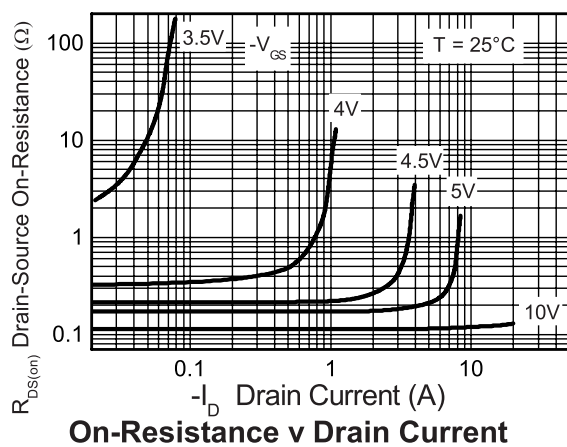
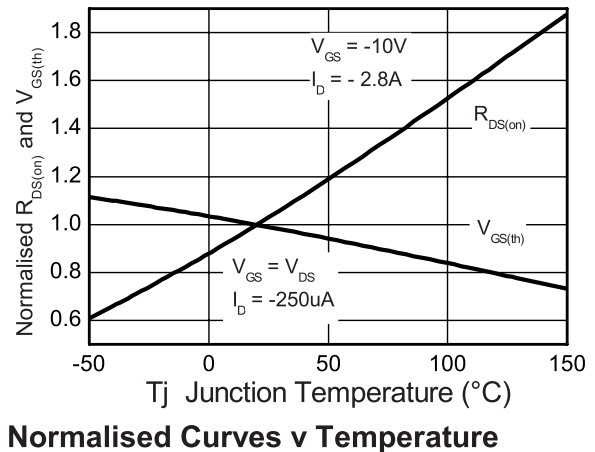
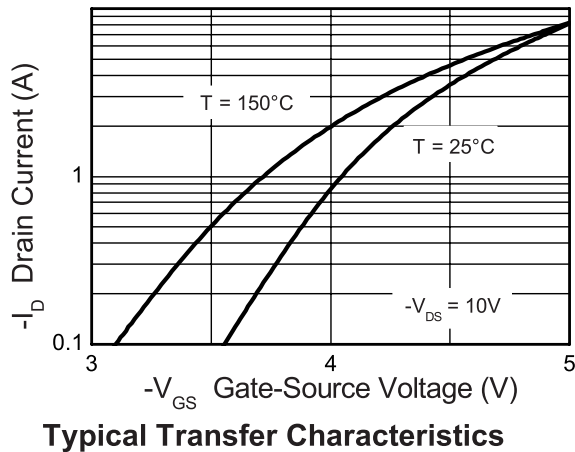
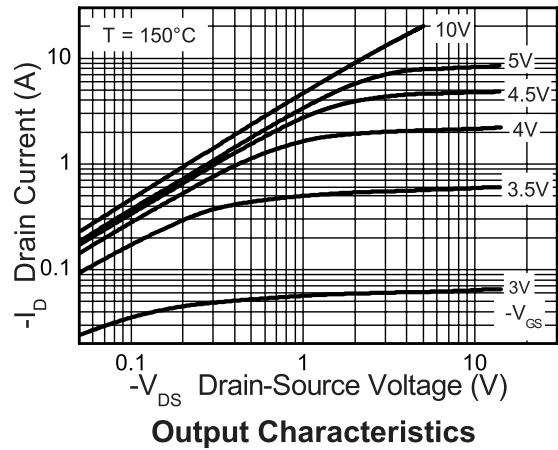
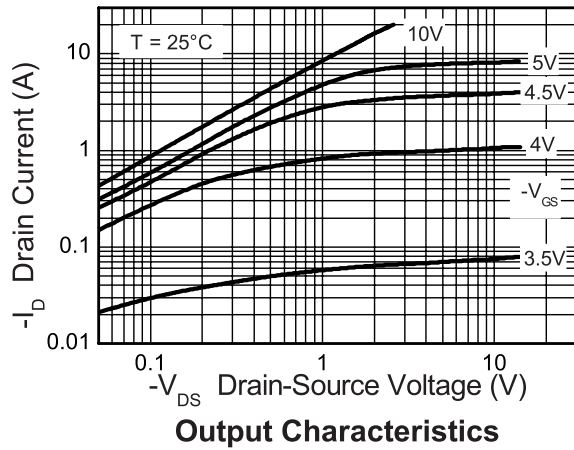
### NOTES:

(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$

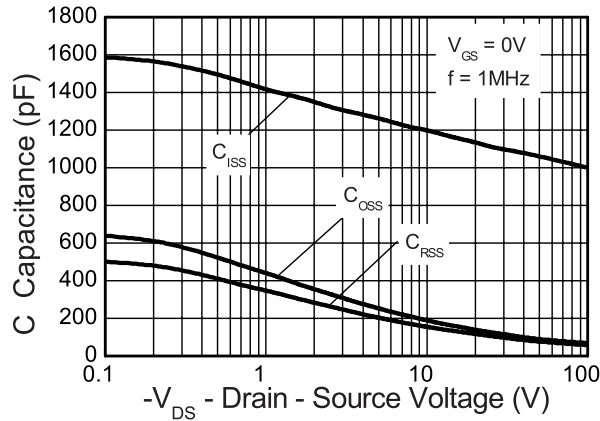
(†) Switching characteristics are independent of operating junction temperature.

(‡) For design aid only, not subject to production testing.

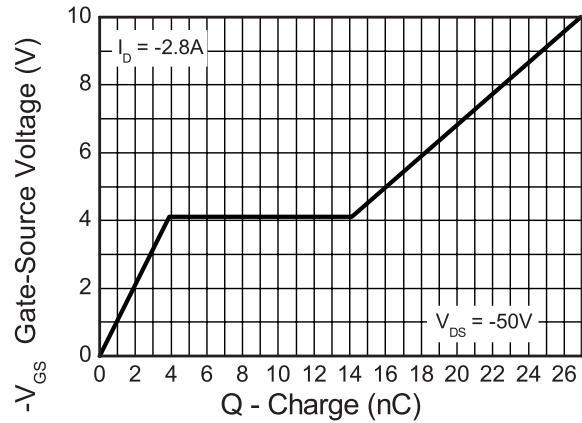
## Typical characteristics



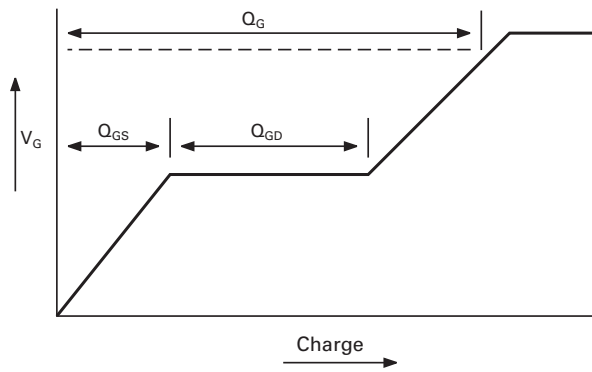
## Typical characteristics



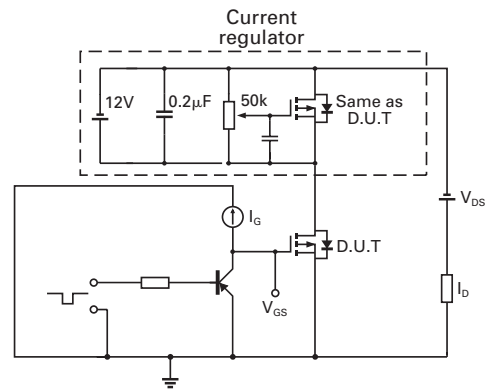
Capacitance v Drain-Source Voltage



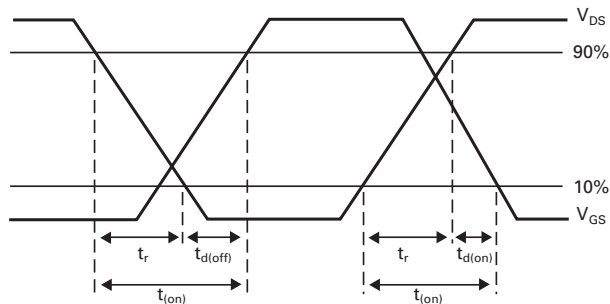
Gate-Source Voltage v Gate Charge



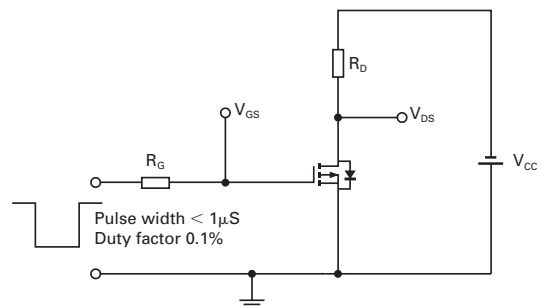
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



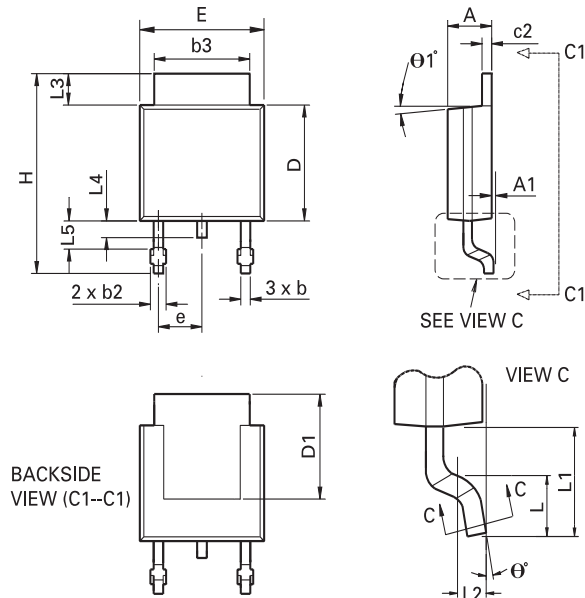
Switching time test circuit

# ZXMP10A18K

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# ZXMP10A18K

## Package outline - DPAK



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	theta 1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	theta 0°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

**Note:** Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

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